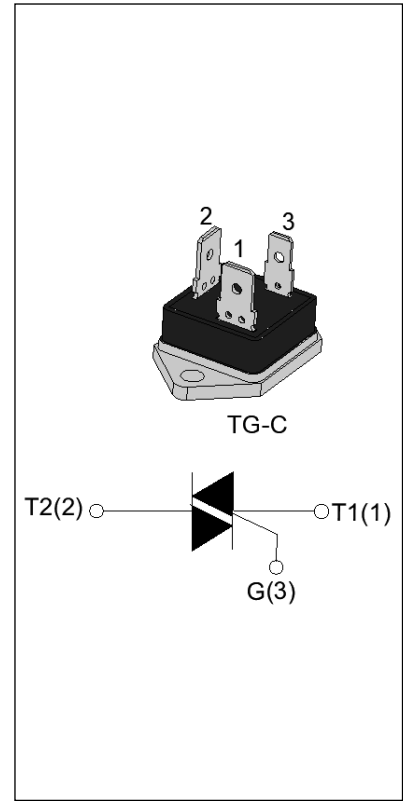


JST41T-1200BW 40A TRIAC

Rev.A.1.0

DESCRIPTION:

The JST41T-1200BW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. JST41T-1200BW snubberless triac is especially recommended for use on inductive loads. By using a DBC, JST41T-1200BW provides a rated insulation voltage of 2500 VRMS, complying with UL standards (File ref: E252906). Package TG-C is RoHS compliant.


MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	40	A
V_{DRM}/V_{RRM}	1200	V
$I_{GT I/II/III}$	50/50/50	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	1200	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	1200	V
RMS on-state current ($T_c \leq 89^\circ\text{C}$)	$I_{T(RMS)}$	40	A
Non repetitive surge peak on-state current (full cycle, $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	420	A
Non repetitive surge peak on-state current (full cycle, $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		462	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	1000	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	di/dt	100	$\text{A}/\mu\text{s}$
Peak gate current ($t_p=20\mu\text{s}$, $T_j=125^\circ\text{C}$)	I_{GM}	8	A
Average gate power dissipation ($T_j=125^\circ\text{C}$)	$P_{G(AV)}$	0.5	W

Peak gate power	P_{GM}	40	W
Peak pulse voltage ($T_j=25^{\circ}C$; non-repetitive, off-state; FIG.7)	V_{pp}	2	kV

ELECTRICAL CHARACTERISTICS($T_j=25^{\circ}C$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V R_L=33\Omega$	I - II -III	MAX.	50	mA
V_{GT}		I - II -III	MAX.	1.3	V
V_{GD}	$V_D=V_{DRM} T_j=125^{\circ}C$ $R_L=3.3K\Omega$	I - II -III	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	I -III	MAX.	80	mA
		II		200	
I_H	$I_T=500mA$		MAX.	100	mA
dV/dt	$V_D=800V$ Gate Open $T_j=125^{\circ}C$		MIN.	1500	V/ μs
(dI/dt) _c	(dV/dt) _c =20V/ μs $T_j=125^{\circ}C$		MIN.	25	A/ms
t_{on}	$I_G=80mA I_A=400mA I_R=40mA$ $T_j=25^{\circ}C$		TYP.	10	μs
t_{off}				70	

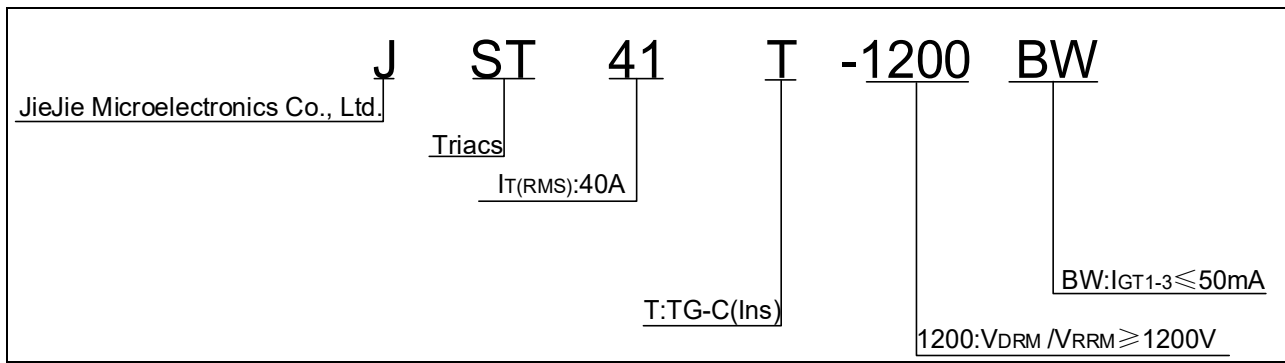
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=60A t_p=380\mu s$	$T_j=25^{\circ}C$	1.4	V
V_{TO}	Threshold voltage	$T_j=125^{\circ}C$	0.74	V
R_D	Dynamic resistance	$T_j=125^{\circ}C$	20	m Ω
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^{\circ}C$	10	μA
I_{RRM}		$T_j=125^{\circ}C$	6	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	0.7	$^{\circ}C/W$
$R_{th(j-a)}$	junction to ambient (AC)	50	$^{\circ}C/W$

ORDERING INFORMATION



MARKING

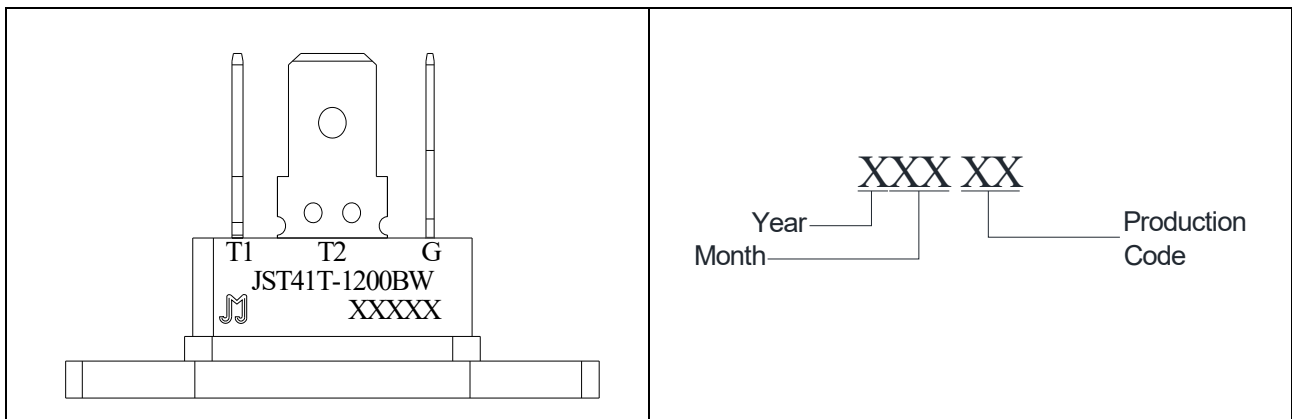


FIG.1 Maximum power dissipation versus RMS on-state current

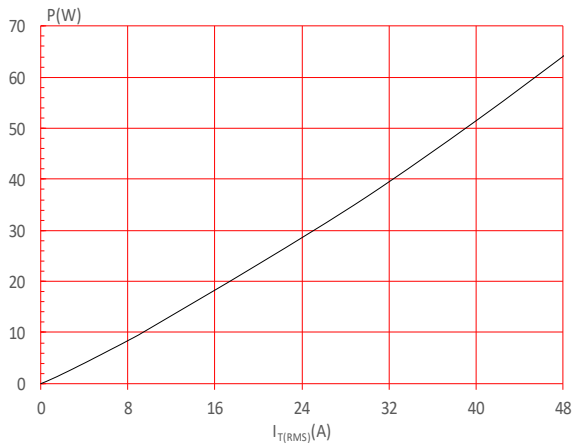


FIG.3: Surge peak on-state current versus number of cycles

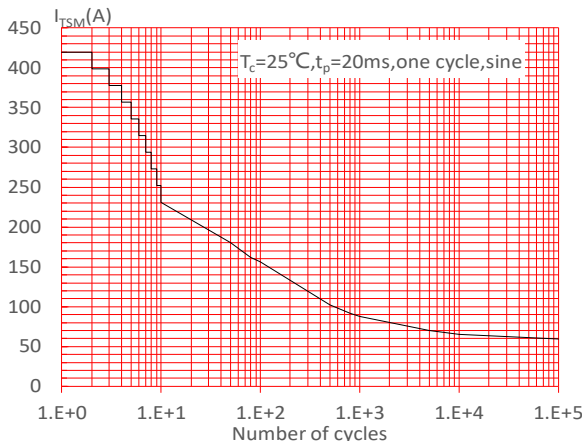


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($di/dt < 100\text{A}/\mu\text{s}$)

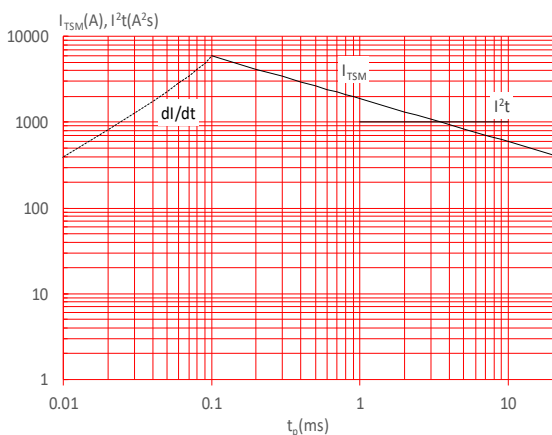


FIG.2: RMS on-state current versus case temperature

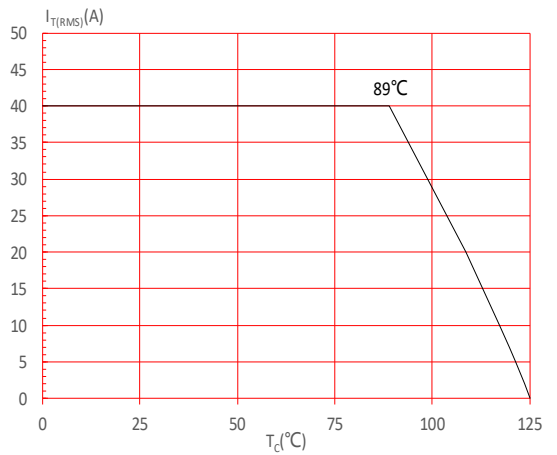


FIG.4: On-state characteristics

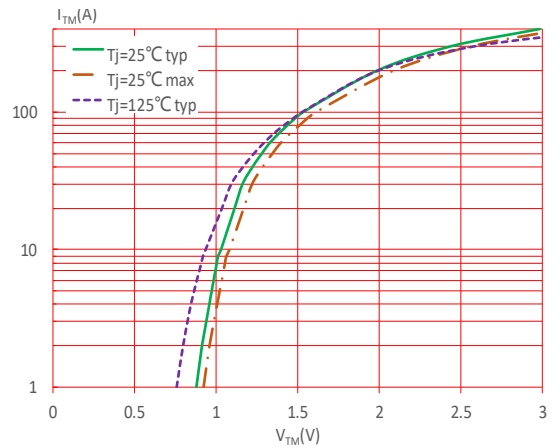


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

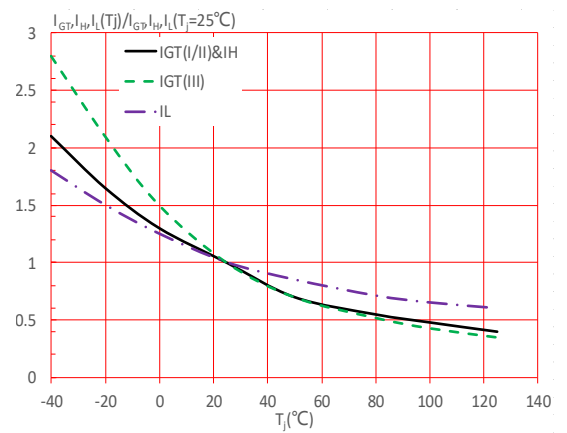
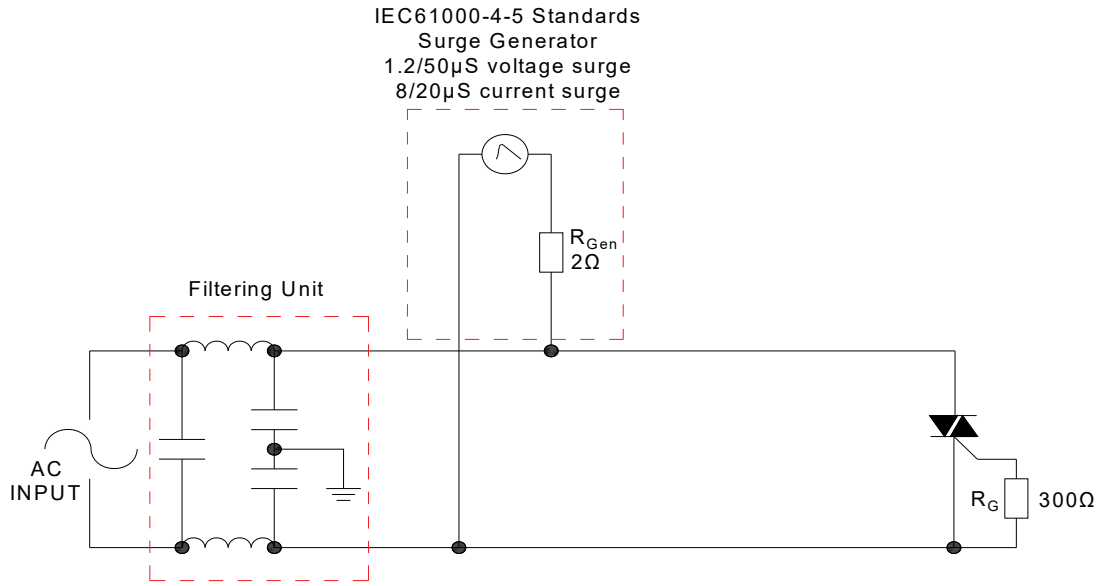


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



SHAPING AND SOLDERING PARAMETERS

Refer to 《Instructions for installation of plastic-sealed in-line power devices》 released by JieJie

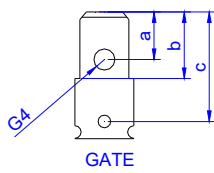
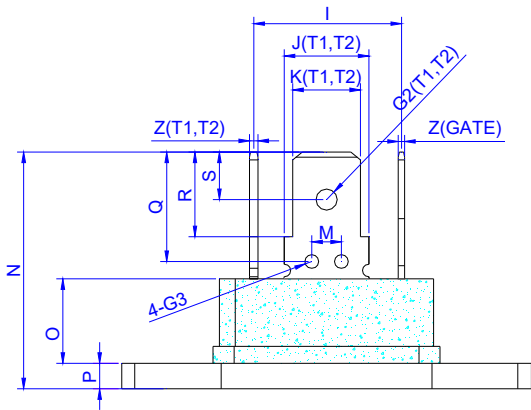
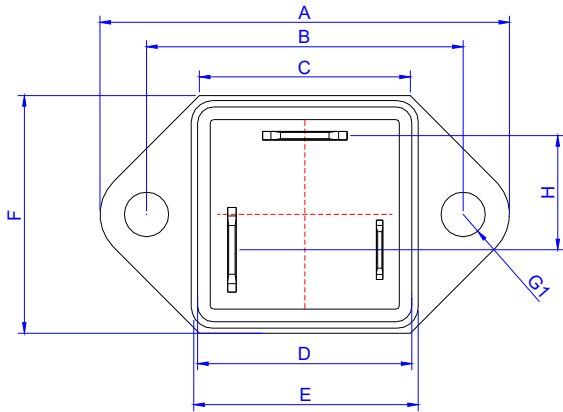
ORDERING INFORMATION

Order code	Voltage $V_{DRM}/V_{RRM}(V)$	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		I - II - III			
JST41T-1200BW	1200	50	TG-C(Ins)	10	Tube

Document Revision History

Date	Revision	Changes
Apr.11, 2023	A.1.0	Last updated

PACKAGE MECHANICAL DATA



TG-C

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			39.2			1.543
B	29.8	30.0	30.2	1.173	1.181	1.189
C			20.2			0.795
D			20.5			0.807
E			21.6			0.85
F			23			0.905
G1	Φ4.1	Φ4.2	Φ4.3	Φ0.161	Φ0.165	Φ0.169
H		10.3			0.406	
I		13.9			0.547	
J(T1,T2)		8			0.315	
K(T1,T2)		6.4			0.252	
M	2.7	3.0	3.3	0.106	0.118	0.130
N			22.8			0.898
O		8.2			0.323	
P		2.5			0.098	
Q	9.45	9.75	10.1	0.374	0.383	0.398
R	7.8	7.95	8.1	0.307	0.313	0.319
S	4.3	4.5	4.7	0.169	0.177	0.185
Z(T1,T2)	0.78	0.8	0.85	0.0307	0.0315	0.0335
G2(T1,T2)		Φ2	Φ2.2		Φ0.079	Φ0.087
G3	Φ1.1	Φ1.3	Φ1.5	Φ0.043	Φ0.051	Φ0.059
G4		Φ1.55	Φ1.75		Φ0.061	Φ0.069
a	2.95	3.15	3.35	0.116	0.124	0.132
b	6.2	6.35	6.5	0.244	0.25	0.256
c	9.35	9.75	10	0.368	0.384	0.393
Z(GATE)	0.58	0.6	0.65	0.0228	0.0236	0.0256
J(GATE)		5.6			0.221	
K(GATE)		4.65			0.183	

DELIVERY MODE

PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON (PCS)
TG-C	TUBE	10	100	500

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